# 2SB0933 (2SB933)

### Silicon PNP epitaxial planar type

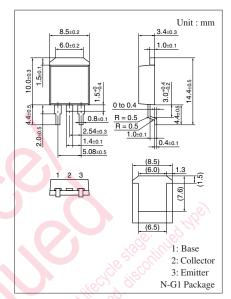
For Power switching Complementary to 2SD1256

#### Features

- $\bullet$  Low collector-emitter saturation voltage  $V_{CE(sat)}$
- $\bullet$  Satisfactory linearity of forward current transfer ratio  $h_{\text{FE}}$
- $\bullet$  Large collector current  $I_{C}$
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

Absolute Maximum Hatings $1_{C} = 23 C$						
Parameter	Symbol	Rating	Unit			
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-130	V			
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-80	V			
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	-7	V			
Collector current	I <sub>C</sub>	-5	A			
Peak collector current	I <sub>CP</sub>	-10	A			
Collector power	P <sub>C</sub>	40	W			
dissipation $T_a = 25^{\circ}C$		1.3				
Junction temperature	Tj	150	°C			
Storage temperature	T <sub>stg</sub>	-55 ~ +150	°C			

#### Absolute Maximum Ratings $T_C = 25^{\circ}C$



Note) Self-supported type package is also prepared.

### Electrical Characteristics $T_c = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = 0$	-80			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -100 \text{ V}, I_E = 0$			-10	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{EB} = -5 V, I_C = 0$			-50	μΑ
Forward current transfer ratio	h <sub>FE1</sub>	$V_{CE} = -2 \text{ V}, \text{ I}_{C} = -0.1 \text{ A}$	45			
No.	h <sub>FE2</sub> *	$V_{CE} = -2 V, I_C = -2 A$	90		260	
Base-emitter voltage	V <sub>BE(sat)</sub>	$I_{\rm C} = -4$ A, $I_{\rm B} = -0.2$ A			-1.5	V
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -4$ A, $I_{\rm B} = -0.2$ A			- 0.5	V
Transition frequency	f <sub>T</sub>	$V_{CE} = -10 \text{ V}, I_C = -0.5 \text{ A}, f = 10 \text{ MHz}$		30		MHz
Turn-on time	t <sub>on</sub>	$I_{\rm C} = -2  {\rm A},$		0.13		μs
Storage time	t <sub>stg</sub>	$I_{B1} = -0.2 \text{ A}, I_{B2} = 0.2 \text{ A}$		0.5		μs
Fall time	t <sub>f</sub>	$V_{CC} = -50 \text{ V}$		0.13		μs

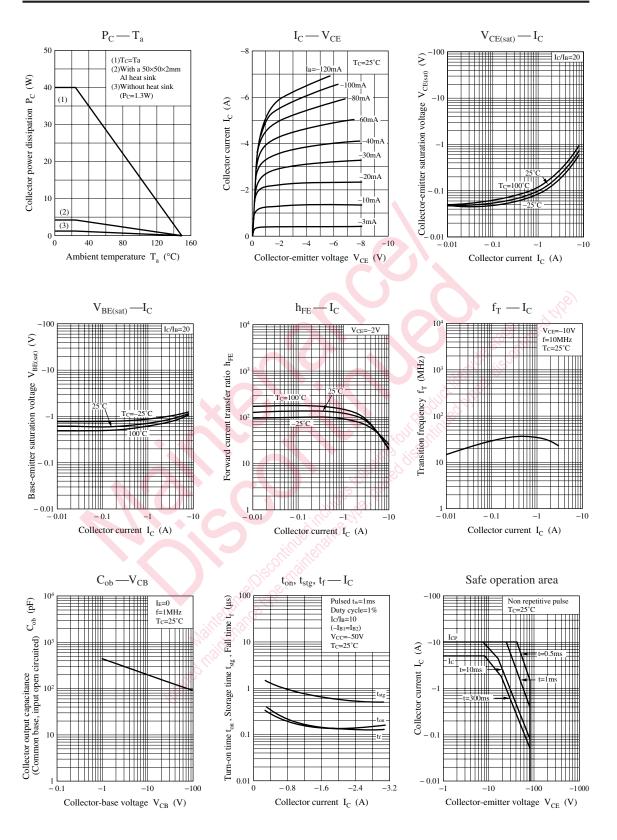
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

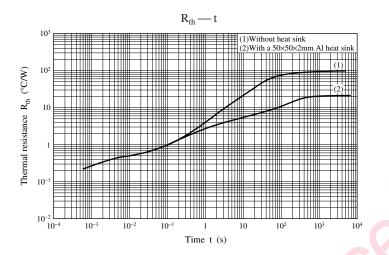
2. \*: Rank classification

Rank	Q	Р
h <sub>FE2</sub>	90 to 180	130 to 260

Note) The part number in the parenthesis shows conventional part number.

### **Panasonic**





loaned maintenance type.

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